

18 December 2013

Product data sheet

#### 1. **General description**

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. **Features and benefits**

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection
- AEC-Q101 qualified

### **Applications**

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	80	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	2.8	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 1.9 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	175	230	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain	7 7	
3	G	gate		G T
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255
7	D	drain		
8	S	source		

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB215ENEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB215ENEA	2B

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	80	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	2.8	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	1.9	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	1.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	7.6	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 0.27 A; DUT in avalanche (unclamped)		-	11.3	mJ
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.6	W
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.3	W
		T <sub>sp</sub> = 25 °C		-	15.6	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain diode						
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.8	Α
ESD maximum rating						
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Measured between all pins.

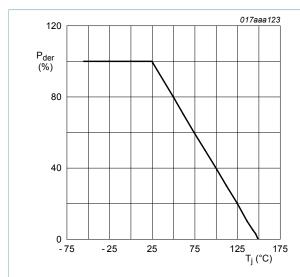


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

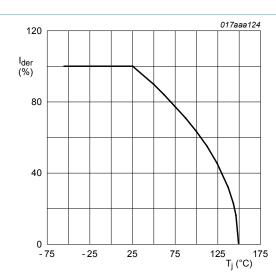


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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### 80 V, single N-channel Trench MOSFET

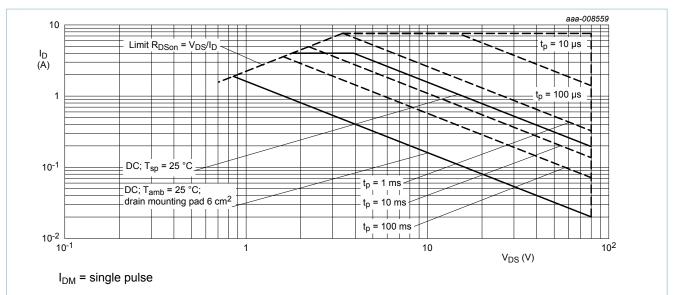


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
11(J-a)	thermal resistance	_	[1]	-	245	282	K/W
	from junction to		<u>[2]</u>	-	68	78	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	33	38	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	4	8	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

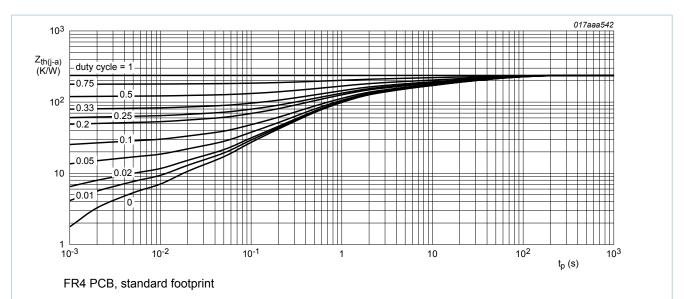


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

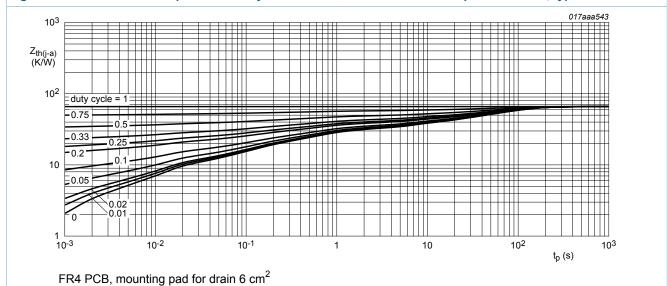


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		l l			
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	1.3	1.7	2.7	V
I <sub>DSS</sub> dr	drain leakage current	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	15	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-15	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; $I_D$ = 1.9 A; $T_j$ = 25 °C	-	175	230	mΩ
resist	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 1.9 A; T <sub>j</sub> = 150 °C	-	340	445	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1.8 A; T <sub>j</sub> = 25 °C	-	195	275	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1.9 A; T <sub>j</sub> = 25 °C	-	7	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	1	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 40 V; I <sub>D</sub> = 1.9 A; V <sub>GS</sub> = 10 V;	-	4.8	7.2	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.6	-	nC
$Q_{GD}$	gate-drain charge		-	0.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 40 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	215	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	25	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	15	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 40 V; I <sub>D</sub> = 1.9 A; V <sub>GS</sub> = 10 V;	-	3.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	9.5	-	ns
t <sub>f</sub>	fall time		-	3	-	ns
Source-d	rain diode		I	1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 0.8 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.8	1.2	V

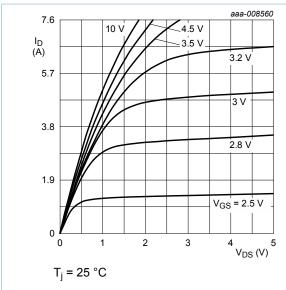


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

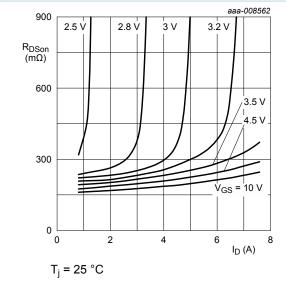


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

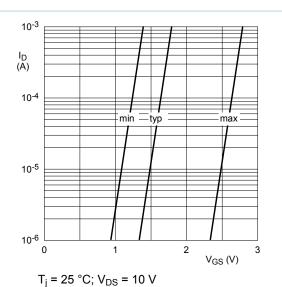


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

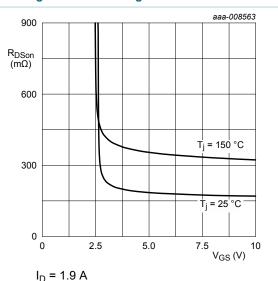


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

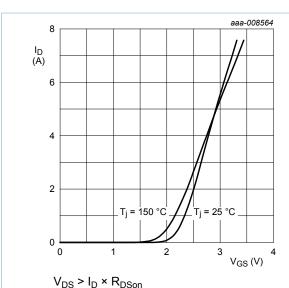


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

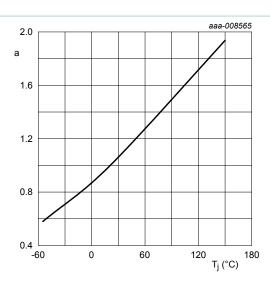


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

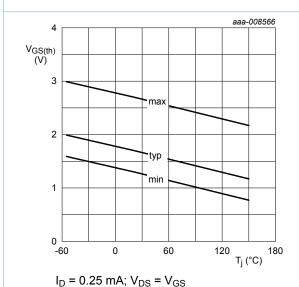
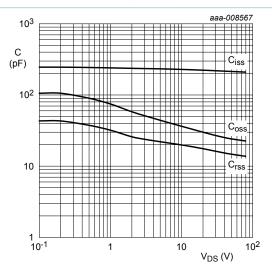


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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### 80 V, single N-channel Trench MOSFET

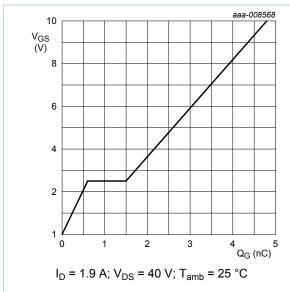


Fig. 14. Gate-source voltage as a function of gate charge; typical values

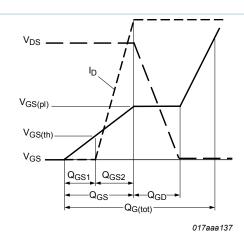


Fig. 15. MOSFET transistor: Gate charge waveform definitions

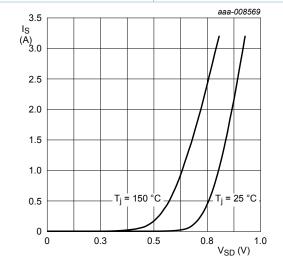
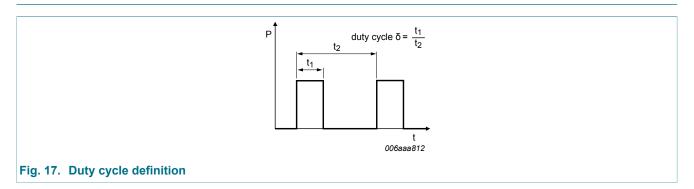


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

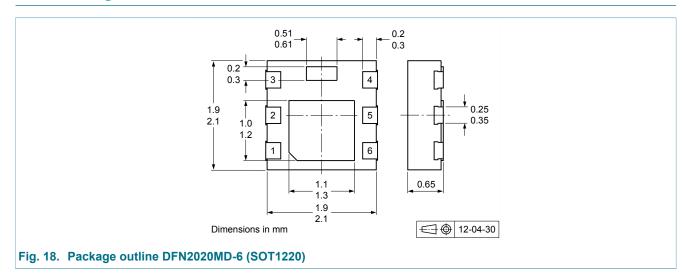
### 11. Test information



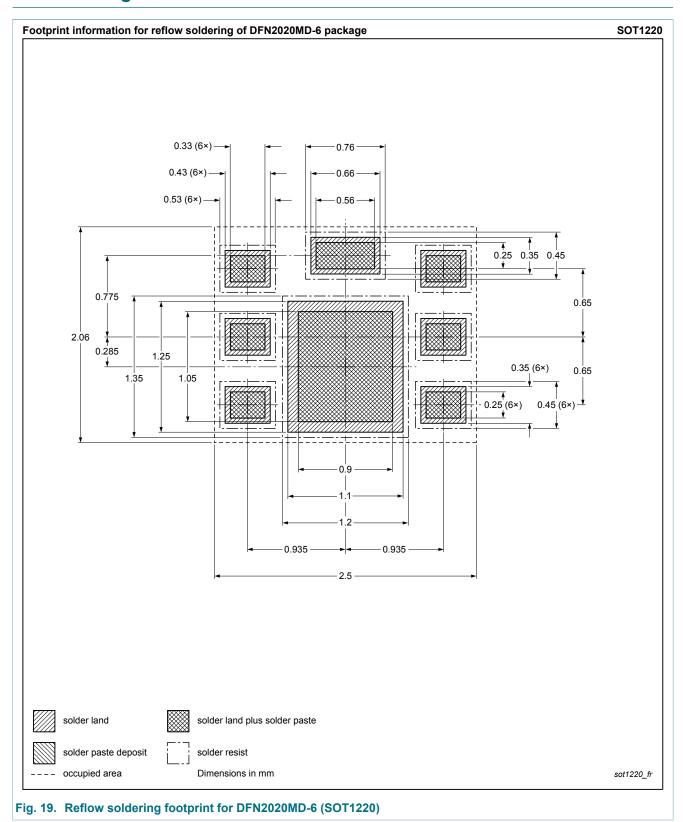
### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



## 13. Soldering



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## 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB215ENEA v.2	20131218	Product data sheet	-	PMPB215ENEA v.1
			_	TIVII DZIJENEA V.I
Modifications:	<ul> <li>Product status char</li> </ul>	nged		
PMPB215ENEA v.1	20130219	Objective data sheet	-	-

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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